

Amendments to the Specification:

Kindly replace the paragraph on page 2, lines 2-5, with the following amended paragraph:

In light of the above, there has been a proposal of adding a sintering auxiliary agent for increasing the sintering density. For example, the publication of Japanese Patent Laid Open Publication No. 2000-247739 describes an attempt of increasing the relative density to 85% to 90% by adding 0.001mol% to 0.5mol% of Bi_2O_3 .

Kindly replace the paragraph on page 2, lines 20-30, with the following amended paragraph:

The present invention provides ~~1. A~~ a SrRuO_3 conductive oxide sintered body characterized in that the relative density is 93% or more; ~~2. A conductive oxide sintered body according to paragraph 1 above, characterized in that the resistivity is $500\mu\Omega\text{cm}$ or less; 3. A conductive oxide sintered body according to paragraph 1 above, characterized in that the resistivity is or $300\mu\Omega\text{cm}$ or less; 4. A~~ The conductive oxide sintered body according to each of paragraphs 1 to 3 above, characterized in ~~containing~~ contains 0.3mol% to 1.2mol% of Bi_2O_3 ; and 5. A conductive oxide sintered body according to each of paragraphs 1 to 3 above, characterized in ~~containing~~ or 0.5mol% (and above) to 1.0mol% of Bi_2O_3 .

Kindly replace the paragraph on page 3, lines 1-11, with the following amended paragraph:

The present invention further provides ~~6. A~~ a sputtering target formed from a SrRuO_3 conductive oxide sintered body characterized in that the relative density is 93% or more; ~~7. A sputtering target formed from a SrRuO_3 conductive oxide sintered body according to paragraph 6 above, characterized in that the resistivity is $500\mu\Omega\text{cm}$ or less; 8. A sputtering target formed from a SrRuO_3 conductive oxide sintered body according to paragraph 6 above, characterized in that the resistivity is or $300\mu\Omega\text{cm}$ or less; 9. A~~ The sputtering target formed from a conductive oxide sintered body according to each of paragraphs 6 to 8 above, characterized in ~~containing~~ contains 0.3mol% to 1.2mol% of Bi_2O_3 ; and ~~10. A sputtering target formed from a conductive oxide sintered body according to each of paragraphs 6 to 8 above, characterized in containing~~ or 0.5mol% (and above) to 1.0mol% of Bi_2O_3 .

Kindly replace the paragraph on page 3, lines 12-27, with the following amended paragraph:

The present invention additionally provides ~~11. A~~ a manufacturing method of a SrRuO_3 conductive oxide sintered body or a sputtering target formed from the sintered body, characterized in that 0.3mol% to 1.2mol% of Bi_2O_3 is added as a sintering auxiliary upon manufacturing the SrRuO_3 conductive oxide sintered body; ~~12. A manufacturing method of a SrRuO_3 conductive oxide sintered body or a sputtering target formed from the sintered body, characterized in that or~~ 0.5mol% (and above) to 1.0mol% of Bi_2O_3 is added as a sintering auxiliary upon manufacturing the SrRuO_3 conductive oxide sintered body; ~~13. A~~ The manufacturing method of a SrRuO_3 conductive oxide sintered body or a sputtering target formed from the sintered body [,] is characterized in that sintering is performed at a sintering temperature of 1400 to 1700°C upon manufacturing the SrRuO_3 conductive oxide sintered body; ~~14. A manufacturing method of a SrRuO_3 conductive oxide sintered body or a sputtering target formed from the sintered body according to paragraph 11 or paragraph 12 above, characterized in that sintering is performed at a sintering temperature of 1400 to 1700°C upon manufacturing the SrRuO_3 conductive oxide sintered body.~~

Kindly replace the paragraph on page 4, lines 19-23, with the following amended paragraph:

Upon manufacturing the SrRuO_3 conductive oxide sintered body of the present invention, 0.3mol% to 1.2mol% of Bi_2O_3 is added as an auxiliary agent. Preferably, sintering is performed upon adding 0.5mol% (and above) to 1.0mol% of Bi_2O_3 . Thereby, 0.3mol% to 1.2mol% of Bi_2O_3 , preferably 0.5mol% (and above) to 1.0mol% of Bi_2O_3 is contained in the SrRuO_3 conductive oxide sintered body and sputtering target.

Kindly replace the paragraph on page 4, lines 24-27, with the following amended paragraph:

In order to improve the sinterability and obtain a high density SrRuO_3 conductive oxide sintered body, it is necessary to add 0.3mol% or more of Bi_2O_3 , and preferably more than 0.5mol% of Bi_2O_3 is added. If less than 0.3mol% of Bi_2O_3 is added, it is not possible to achieve a density of 93% or more.

Kindly replace the paragraph on page 4, line 28, to page 5, line 4, with the following amended paragraph:

However, when the Bi_2O_3 contained in the SrRuO_3 conductive oxide sintered body and sputtering target increases, the Bi_2O_3 contained in the sputtering film will increase, and the resistivity tends to increase. Moreover, when the amount of addition exceeds 1.2mol%, a second layer is formed in the sputtering film, this generates a Bi compound at the boundary face with the BSTO film or PZT film, and causes a problem of deteriorating the dielectric property. In consideration of the above, the upper limit of the additive amount has been set to 1.2mol%, and preferably to 1.0mol%.